

STH240N75F3-2, STH240N75F3-6

N-channel 75 V, 2.6 mΩ typ., 180 A STripFET™ III Power MOSFET in H²PAK-2 and H²PAK-6 packages

Datasheet - production data

Features

Order code	V _{DSS}	R _{DS(on)} max.	I _D
STH240N75F3-2	75 V	< 3.0 mΩ	180 A
STH240N75F3-6	75 V	< 0.0 III <u>s</u> 2	100 A

- Conduction losses reduced
- Low profile, very low parasitic inductance

Applications

■ Switching application

Description

These devices are N-channel enhancement mode Power MOSFETs produced using STMicroelectronics' STripFET™ III technology, which is specifically designed to minimize onresistance and gate charge to provide superior switching performance.

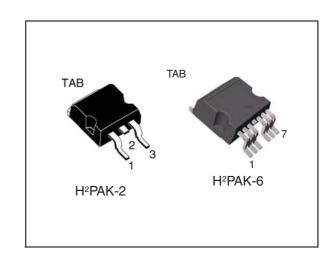


Figure 1. Internal schematic diagram

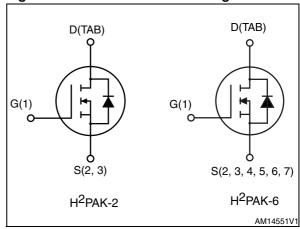


Table 1. Device summary

Order code	Marking	Package	Packaging
STH240N75F3-2	240N75F3	H ² PAK-2	Tana and rool
STH240N75F3-6	24011/5F3	H ² PAK-6	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit	
V _{DS}	Drain-source voltage	75	V	
V _{GS}	Gate-source voltage	± 20	V	
I _D ⁽¹⁾	Drain current (continuous) at T _C = 25 °C	180	Α	
I _D	Drain current (continuous) at T _C = 100 °C	170	Α	
I _{DM} ⁽²⁾	Drain current (pulsed)	720	Α	
P _{TOT}	Total dissipation at T _C = 25 °C	300	W	
	Derating factor	2	W/°C	
E _{AS} (3)	Single pulse avalanche energy	600	mJ	
T _{stg}	Storage temperature	55 to 175	°C	
Tj	Operating junction temperature	-55 to 175		

- 1. Current limited by package.
- 2. Pulse width limited by safe operating area.
- 3. Starting Tj = 25 °C, I_D = 60 A, V_{DD} = 15 V.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	0.5	°C/W
R _{thj-pcb} (1)	Thermal resistance junction-pcb max	35	°C/W

1. When mounted on 1 inch2 FR-4 2 oz Cu.

2 Electrical characteristics

(Tcase = 25 °C unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 250 μA, V _{GS} = 0	75			V
I _{DSS}	Zero gate voltage drain current	$V_{DS} = 75 \text{ V},$ $V_{DS} = 75 \text{ V}, T_{C} = 125 ^{\circ}\text{C},$ $V_{GS} = 0$			10 100	μ Α μ Α
I _{GSS}	Gate body leakage current	$V_{DS} = \pm 20 \text{ V}, V_{DS} = 0$			±200	nA
V _{GS(th)}	_	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	V
R _{DS(on)}	Static drain-source on- resistance	V _{GS} = 10 V, I _D = 90 A		2.6	3.0	mΩ

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25 \text{ V, f} = 1 \text{ MHz, V}_{GS} = 0$	-	6800 1100 50	-	pF pF pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 37.5 V, I_{D} = 120 A, V_{GS} = 10 V (see <i>Figure 14</i>)	ı	87 30 26	ı	nC nC nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time Rise time	V _{DD} = 37.5 V, I _D = 60 A	-	25 70	-	ns ns
t _{d(off)}	Turn-off delay time Fall time	R_{G} = 4.7 Ω V_{GS} = 10 V, (see <i>Figure 13</i>)	-	100 15	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current		_		180	Α
I _{SD} ⁽¹⁾	Source-drain current (pulsed)		_		720	Α
V _{SD} (2)	Forward on voltage	I _{SD} = 120 A, V _{GS} = 0	-		1.5	V
t _{rr}	Reverse recovery time	$I_{SD} = 120 \text{ A,di/dt} = 100 \text{ A/}\mu\text{s}$		80		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 30 \text{ V}, T_j = 150 ^{\circ}\text{C}$	-	180		nC
I _{RRM}	Reverse recovery current	(see Figure 15)		4.5		Α

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Thermal impedance

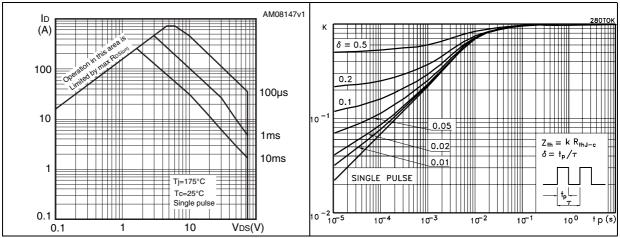


Figure 4. Output characteristics

Figure 5. Transfer characteristics

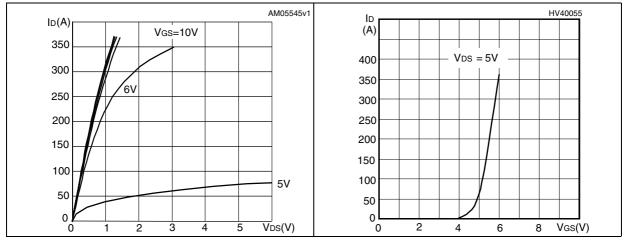
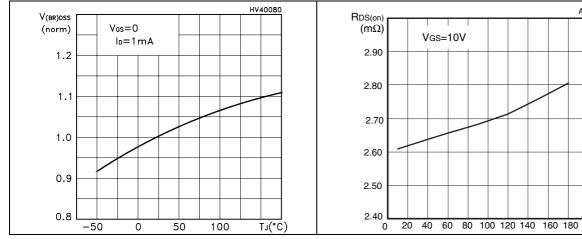


Figure 6. Normalized BV_{DSS} vs temperature Figure 7. Static drain-source on-resistance



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C(pF) $V_{GS}(V)$ f=1MHz $V_{GS} = 0V$ V_{DD}=37.5V 25000 12 I_D=120A 20000 15000 10000 Ciss 5000 40 100 Vps(V) 20 40 60 100 Qg(nC) 0 20 80

Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

Figure 10. Normalized gate threshold voltage Figure 11. Normalized on-resistance vs vs temperature temperature

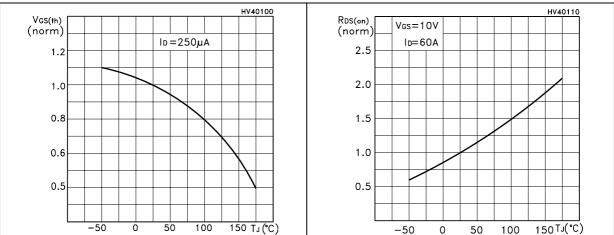
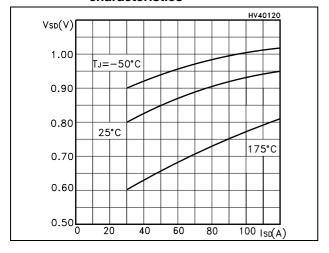


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

Figure 14. Gate charge test circuit

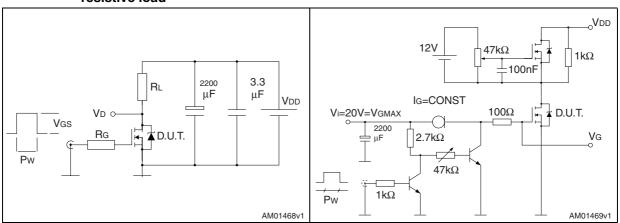


Figure 15. Test circuit for inductive load switching and diode recovery times

Figure 16. Unclamped inductive load test circuit

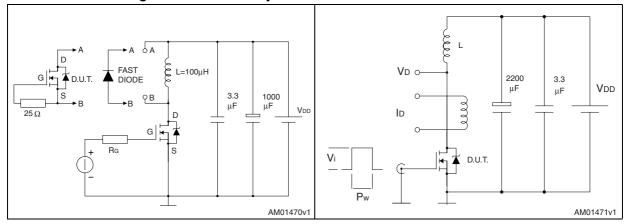
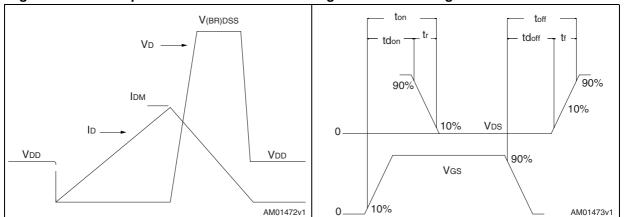


Figure 17. Unclamped inductive waveform

Figure 18. Switching time waveform



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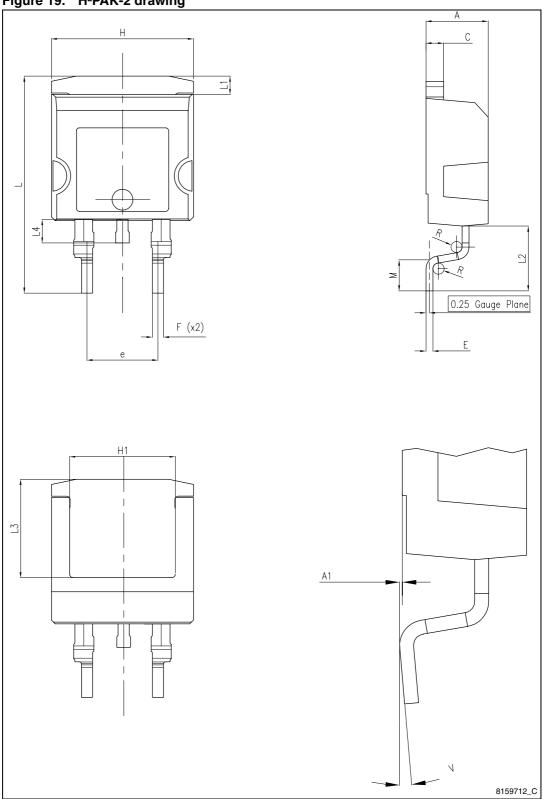
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 8. H²PAK-2 mechanical data

Dim	mm				
Dim.	Min.	Max.			
Α	4.30		4.80		
A1	0.03		0.20		
С	1.17		1.37		
е	4.98		5.18		
E	0.50		0.90		
F	0.78		0.85		
Н	10.00		10.40		
H1	7.40		7.80		
L	15.30	-	15.80		
L1	1.27		1.40		
L2	4.93		5.23		
L3	6.85		7.25		
L4	1.5		1.7		
М	2.6		2.9		
R	0.20		0.60		
V	0°		8°		

Figure 19. H²PAK-2 drawing



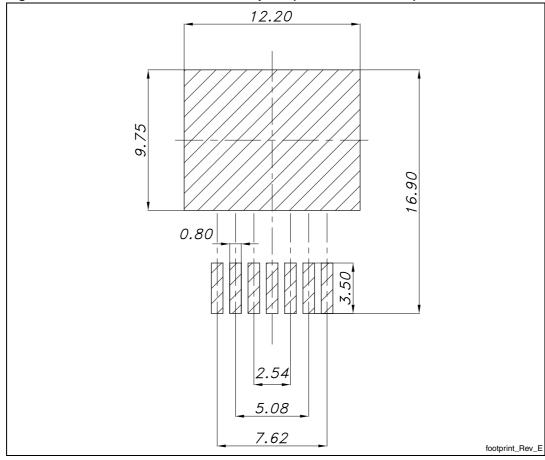
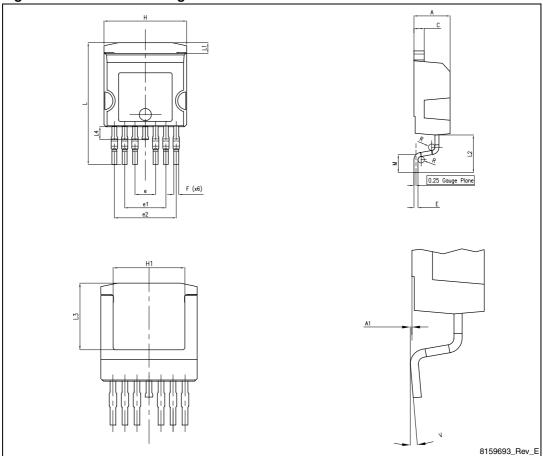


Figure 20. H²PAK-2 recommended footprint (dimensions in mm)

Table 9. H²PAK-6 mechanical data

Dim		mm	
Dim.	Min.	Тур.	Max.
Α	4.30		4.80
A1	0.03		0.20
С	1.17		1.37
е	2.34		2.74
e1	4.88		5.28
e2	7.42		7.82
Е	0.45		0.60
F	0.50		0.70
Н	10.00		10.40
H1	7.40	-	7.80
L	14.75		15.25
L1	1.27		1.40
L2	4.35		4.95
L3	6.85		7.25
L4	1.5		1.75
М	1.90		2.50
R	0.20		0.60
V	0°		8°

Figure 21. H²PAK-6 drawing



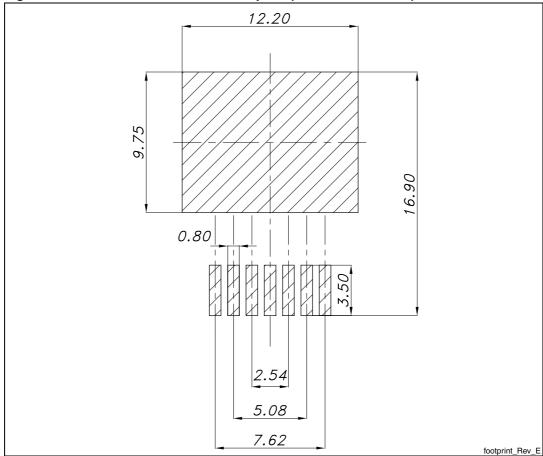


Figure 22. H²PAK-6 recommended footprint (dimensions in mm)

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5 Packaging mechanical data

Table 10. H²PAK-2 and H²PAK-6 tape and reel mechanical data

	Таре			Reel		
D:	n	nm	D:	m	nm	
Dim.	Min.	Max.	— Dim.	Min.	Max.	
A0	10.5	10.7	А		330	
В0	15.7	15.9	В	1.5		
D	1.5	1.6	С	12.8	13.2	
D1	1.59	1.61	D	20.2		
Е	1.65	1.85	G	24.4	26.4	
F	11.4	11.6	N	100		
K0	4.8	5.0	Т		30.4	
P0	3.9	4.1				
P1	11.9	12.1		Base qty	1000	
P2	1.9	2.1		Bulk qty	1000	
R	50					
Т	0.25	0.35				
W	23.7	24.3				

Figure 23. Tape

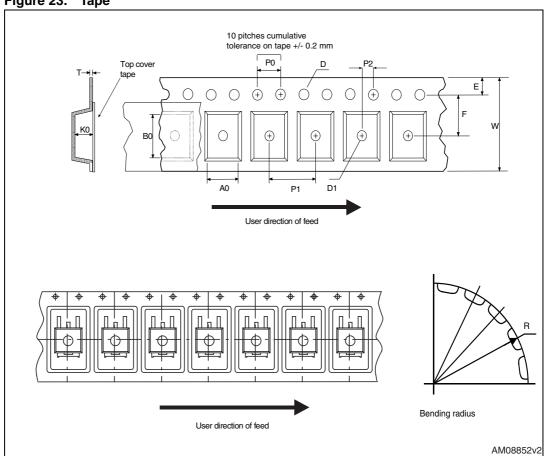
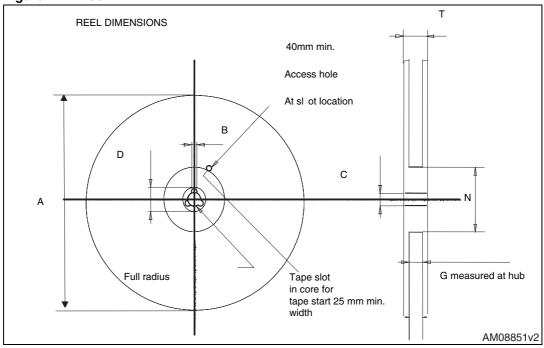


Figure 24. Reel



6 Revision history

Table 11. Document revision history

Date	Revision	Changes
19-Oct-2011	1	Initial release.
02-Jul-2012	2	Added new device in H²PAK-2. Table 1: Device summary has been modified accordingly. Table 8: H²PAK-2 mechanical data, Figure 19: H²PAK-2 drawing and Figure 20: H²PAK-2 recommended footprint (dimensions in mm) have been added. Minor text changes.

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